

## Design Note – DN06023/D

# Universal AC 15 W 4 Cell Charger

**ON Semiconductor** 

Device	Application	Input Voltage	Output Power	Topology	I/O Isolation
MBT3906 MC33340 NCP1055 NIS6111	4 Cell NiCd-NiMH Battery Charger	Universal 90-264 Vac	15 Watt	Flyback	Optional

	Other Specifications							
	Output 1 Output 2 Output 3 Ou							
Output Voltage	5.9 Vdc max	N/A	N/A	N/A				
Ripple	125 mA	N/A	N/A	N/A				
Nominal Current	2.5 A	N/A	N/A	N/A				
Max Current	3.0 A	N/A	N/A	N/A				
Min Current	N/A	N/A	N/A	N/A				

PFC (Yes/No)	NO
Minimum Efficiency	80%
Inrush Limiting / Fuse	750 mA fuse
Operating Temp. Range	0 to +40° C
Cooling Method/Supply Orientation	Case Convection

### **Circuit Description**

This four-cell nickel battery rapid charger is based on the very low cost gated oscillator PWM switcher. The MC33340 -dV/dt detector controls the charging profile. The rapid charge rate current level is set to the maximum by magnetic and the NCP1055 design.

One problem common to all rapid chargers is the dynamic range from trickle charge to rapid rates. The 2.5 A rapid charge is about 100 times the 25 mA trickle.

This design overcomes this by utilizing a timer with an approximate 1% duty cycle to achieve the time averaged 25 mA trickle charge. ON's co-packaged discrete transistors perform the analog functions with very low cost and reasonable temperature stability.

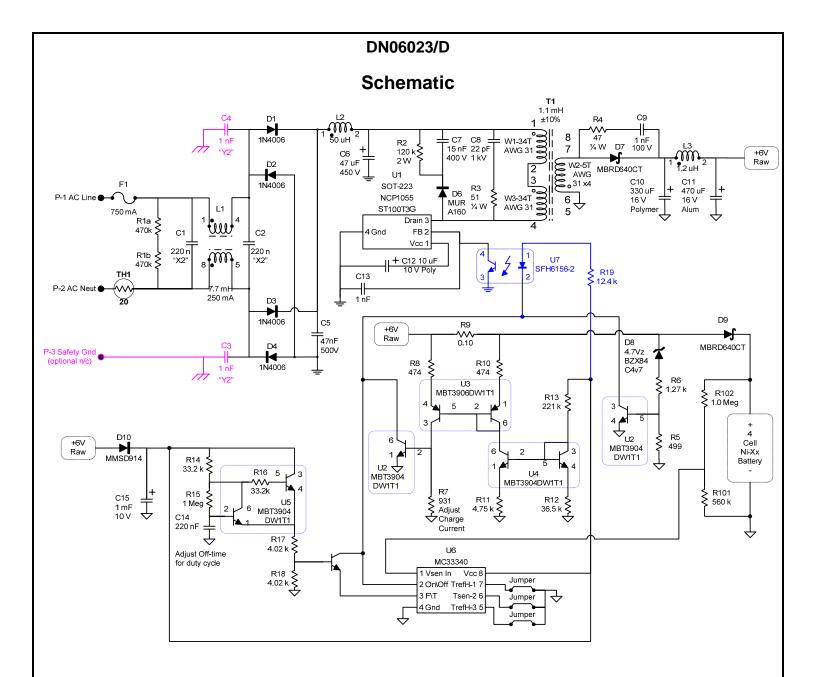
The CCM-DCM boundary is at 142 Vac. European operation will be in DCM while the US will be in CCM. The charger is shown with the optional optocoupler in blue for isolated circuits. For the lowest cost chargers with integrated case isolation barrier systems the optocoupler can be eliminated. Then tie the two DC returns together and U7-2 is connected to U7-4.

The schematic shows optional Y caps in pink for systems with a three-wire power cord. The earth return provides additional margin for applications that require more EMI filtering or earth ground connection.

Blocking diode D9 prevents reverse current from the battery flowing through the low power bias circuitry when the charger is powered off. Efficiency can be improved by eliminating the diode. The NIS6111 BERS rectifier can be used for D7 and D9 to improve efficiency about 7% but at slightly higher cost.

### **Key Features**

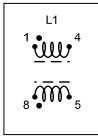
- 2.5 Ampere fast charger.
- Vdc limited open circuit output.
- 100 kHz Switchmode gated oscillator.
- Frequency dithering reduces EMI signature.
- Rapid charge rate current dynamically limited.
- Trickle charge rate is timer duty cycle controlled.
- Very low standby power consumption.



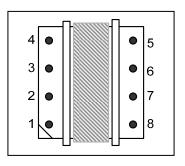
Magnetics Design Data sheet							
Project / Customer	4 Cell Charg	er For Ni-Cd, N	Ni-MH				
Description:	Differential M	Differential Mode Inductor					
Schematic Ref. Des:	L1						
Bobbin:	Vertical 8-Pir	า					
Core:	EE-42211 J		Magnetics Ir	nC.			
Core Gap:	none						
Inductance Magnetizing:	7.7 mH	±5%	100 kHz	Pin 1-4, 5-8			
Inductance Leakage:	110 uH	±5%	100 kHz	Pin 1-4, 5-8 shorted.			

Winding	gs (in order)	Turns	Size	No of Wires	Material
Layer	Winding				
	W1	47			
1	W1	8	23 awg	1	Isonol180
2	W1	8	23 awg	1	Isonol180
3	W1	8	23 awg	1	Isonol180
4	W1	8	23 awg	1	Isonol180
5	W1	8	23 awg	1	Isonol180
6	W1	7	23 awg	1	Isonol180
	W2	47			
1	W2	8	23 awg	1	Isonol180
2	W2	8	23 awg	1	Isonol180
3	W2	8	23 awg	1	Isonol180
4	W2	8	23 awg	1	Isonol180
5	W2	8	23 awg	1	Isonol180
6	W2	7	23 awg	1	Isonol180
HiPot:					
P-S		4 kVac	1 s.		

Schematic



Lead Pin-out



	Magno	etics Desig	yn Data she	et		
Project / Customer	4 Cell Charge	er For Ni-Cd, N	i-MH			
Description:	Common Mo	de Inductor				
Schematic Ref. Des:	L2					
Bobbin:	none					
Core:	T 2/1.3/0.6		General Pur	pose		
Core Gap:	none					
Inductance Magnetizing:	51 uH	±5%	100 kHz	Pin 1-2		
Inductance Leakage:	NA	±5%	100 kHz			
Windings (in order)	Turns	Size	No of W	ïres	Material	

Layer	Winding				
	W1	34			
1	W1	34	34 awg	5	Isonol180

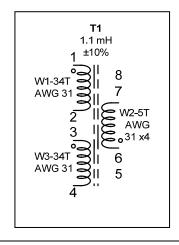
	Magn	etics Desi	gn Data she	et			
Project / Customer	4 Cell Charg	er For Ni-Cd, I	Ni-MH				
Description:	Output filter I	Output filter Inductor					
Schematic Ref. Des:	L3						
Bobbin:	none						
Core:	T 1.2/0.83/0.	5	General Pur	pose			
Core Gap:	none						
Inductance Magnetizing:	1.24 uH	±5%	100 kHz	Pin 1-2			
Inductance Leakage:	NA	±5%	100 kHz				

Winding	gs (in order)	Turns	Size	No of Wires	Material
Layer	Winding				
	W1	6			
1	W1	6	22 awg	5	Isonol180

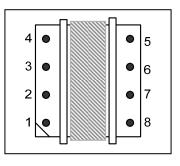
#### **Magnetics Design Data sheet** Project / Customer 4 Cell Charger For Ni-Cd, Ni-MH Description: Transformer Schematic Ref Des: T1 Bobbin: Vertical 8-Pin Core: EE-43007 P Magnetics Inc. Core Gap: TBD 1.1 mH Inductance Magnetizing: 100 kHz Pin 1-4 with 2-3 shorted. ±5% Inductance Leakage: 7 uH ±5% 100 kHz Pin 1-4, 2-3, 5-6-7-8 shorted.

Windings (in order)		Turns	Size	No of Wires	Material
Layer	Winding				
	W1	34			
1	W1	17	23 awg	1	Isonol180
2	W1	17	23 awg	1	Isonol180
3	Tape	3	0.05		PVC
	W2	5			
4	W2	5	23 awg	4	Isonol180
5	Tape	3	0.05		PVC
	W3	34			
6	W3	17	23 awg	1	Isonol180
7	W3	17	23 awg	1	Isonol180
8	Таре	1	0.05		PVC
HiPot:					
P-S		4 kVac	1 s.		
P-Core		4 kVac	1 s.		
S-Core		4 kVac	1 s.		

#### Schematic



Lead Pin-out



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